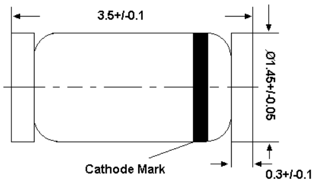
LL352

Silicon Epitaxial Planar Switching Diode

Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance

LL-34



Glass case MiniMELF
Dimensions in mm

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	85	V
Reverse Voltage	V_R	80	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Maximum Peak Forward Current	I_{FM}	200	mA
Peak Forward Surge Current (10 ms)	I_{FSM}	1	A
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 100 mA	V_F	1.2	V
Reverse Leakage Current at V_R = 30 V at V_R = 80 V	I_R	0.1 0.5	µA
Capacitance at V_R = 0, f = 1 MHz	C_{tot}	3	pF
Reverse Recovery Time at I_F = 10 mA to I_R = 1 mA, V_R = 6 V, R_L = 100 Ω	t_{rr}	4	ns

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Dated : 15/06/2009

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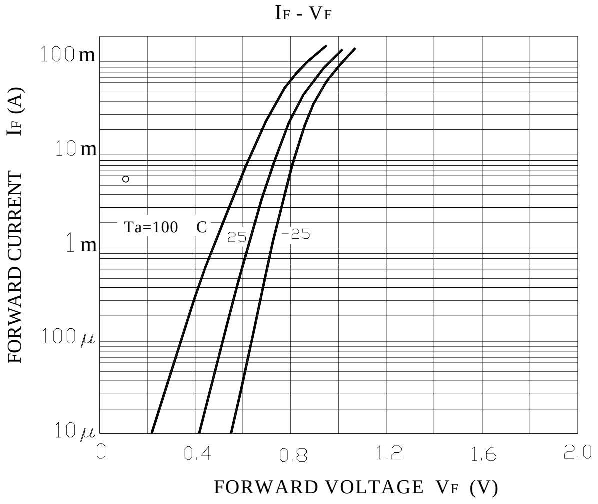
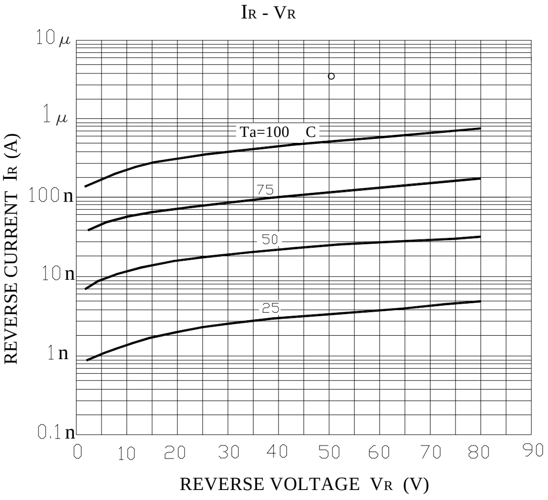
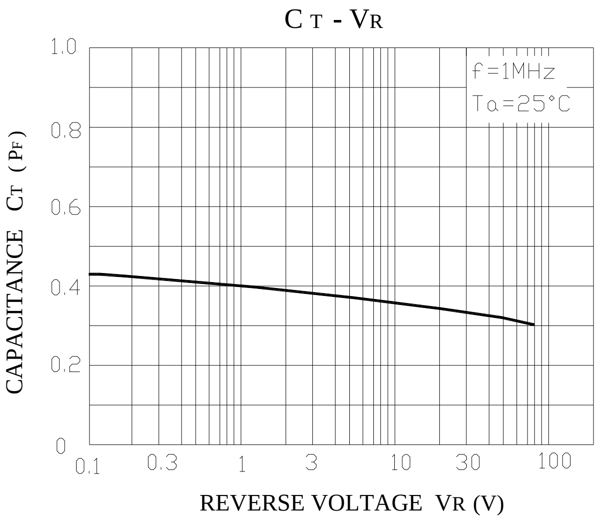

I_F - V_F


I_R - V_R


C_T - V_R

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